(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
13 January 2005 (13.01.2005)

PCT

(10) International Publication Number
WO 2005/004206 A2

(51) International Patent Classification[7]: H01L

(21) International Application Number:
PCT/US2004/021279

(22) International Filing Date: 30 June 2004 (30.06.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/604,206 1 July 2003 (01.07.2003) US

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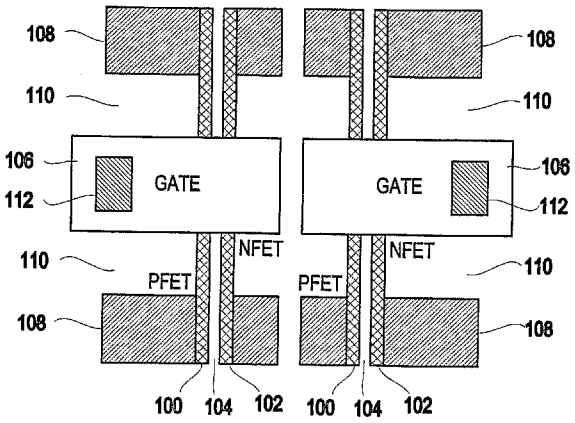
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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),

[Continued on next page]

(54) Title: INTEGRATED CIRCUIT HAVING PAIRS OF PARALLEL COMPLEMENTARY FINFETS



(57) Abstract: A method and structure for an integrated circuit structure that utilizes complementary fin-type field effect transistors (FinFETs) is disclosed. The invention has a first-type of FinFET which includes a first fin (100), and a second-type of FinFET which includes a second fin (102) running parallel to the first fin (100). The invention also has an insulator fin positioned between the source/drain regions (130) of the first first-type of FinFET and the second-type of FinFET. The insulator fin has approximately the same width dimensions as the first fin (100) and the second fin (102), such that the spacing between the first-type of FinFET and the second-type of FinFET is approximately equal to the width of one fin. The invention also has a common gate (106) formed over channel regions of the first-type of FinFET and the second-type of FinFET. The gate (106) includes a first impurity doping region adjacent the first-type of FinFET and a second impurity doping region adjacent the second-type of FinFET. The differences between the first impurity doping region and the second impurity doping region provide the gate with different work functions related to differences between the first-type of FinFET and the second-type of FinFET. The first fin (100) and the second fin (102) have approximately the same width.

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European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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Published:

— *without international search report and to be republished upon receipt of that report*

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